

Ordering number : ENN8342



SANYO Semiconductors

DATA SHEET

2SC6019

 — NPN Epitaxial Planar Silicon Transistor
DC / DC Converter Applications

Applications

- Relay drivers, lamp drivers, motor drivers, flash.

Features

- Adoption of FBET and MBIT processes.
- Large current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- Narrow h_{FE} range.
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}	—	15	V
Collector-to-Emitter Voltage	V_{CEO}	—	15	V
Emitter-to-Base Voltage	V_{EBO}	—	6	V
Collector Current	I_C	—	7	A
Collector Current (Pulse)	I_{CP}	—	10	A
Base Current	I_B	—	600	mA
Collector Dissipation	P_C	—	0.8	W
		$T_c=25^\circ\text{C}$	15	W
Junction Temperature	T_J	—	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	—	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=12\text{V}, I_E=0\text{A}$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0\text{A}$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=2\text{V}, I_C=500\text{mA}$	250		400	
Gain-Bandwidth Product	f_T	$V_{CE}=2\text{V}, I_C=500\text{mA}$		380		MHz

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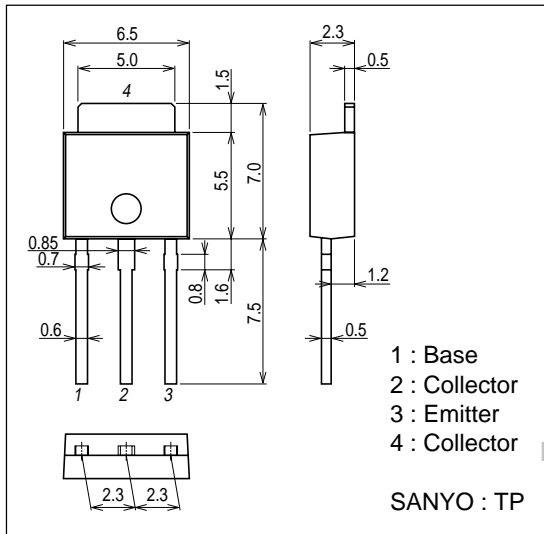
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		23		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =1.5A, I _B =30mA		85	125	mV
		I _C =3A, I _B =60mA		145	215	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =3A, I _B =60mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =10μA, I _E =0A	15			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =1mA, R _{BE} =∞	15			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =10μA, I _C =0A	6			V
Turn-ON Time	t _{on}	See specified Test Circuit.		30		ns
Storage Time	t _{stg}	See specified Test Circuit.		190		ns
Fall Time	t _f	See specified Test Circuit.		15		ns

Package Dimensions

unit : mm

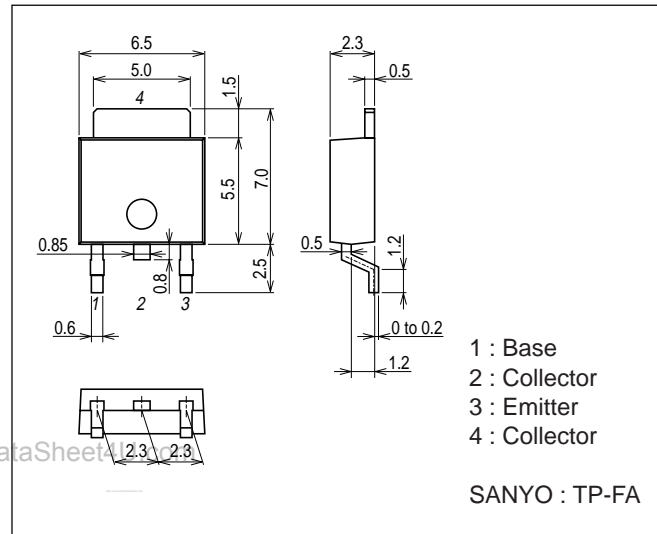
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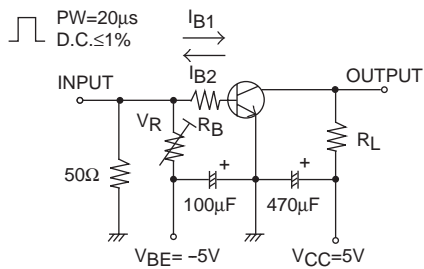
Package Dimensions

unit : mm

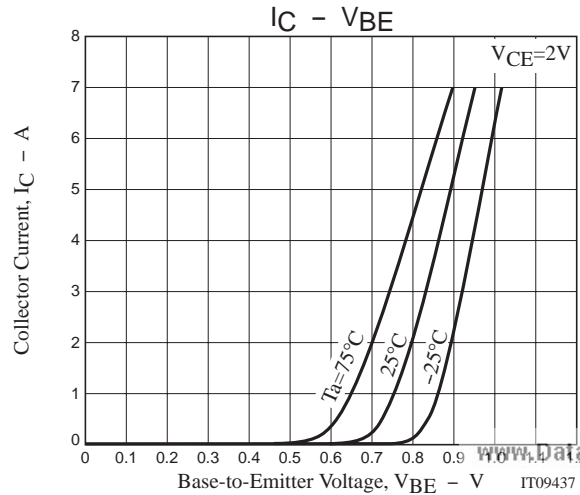
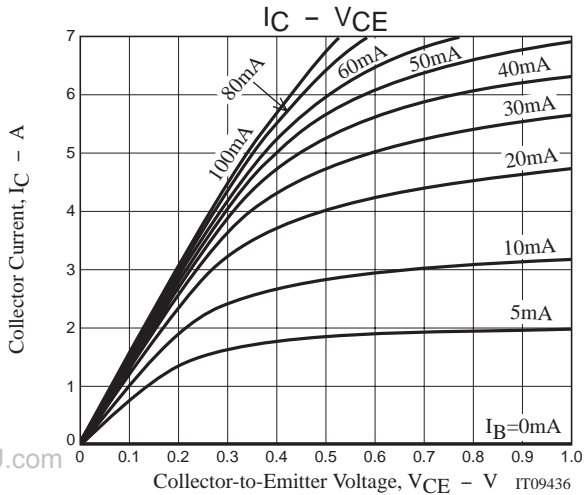
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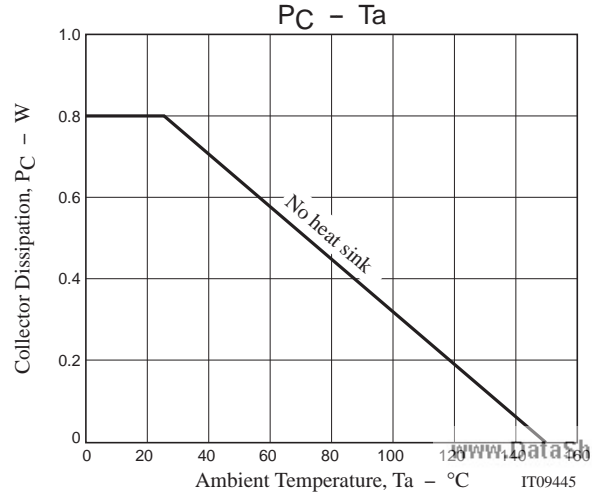
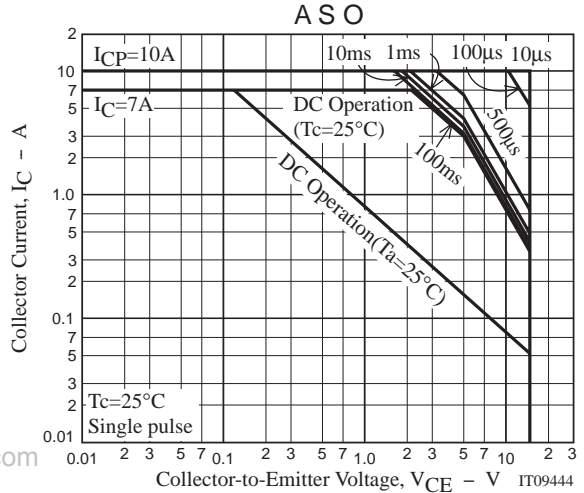
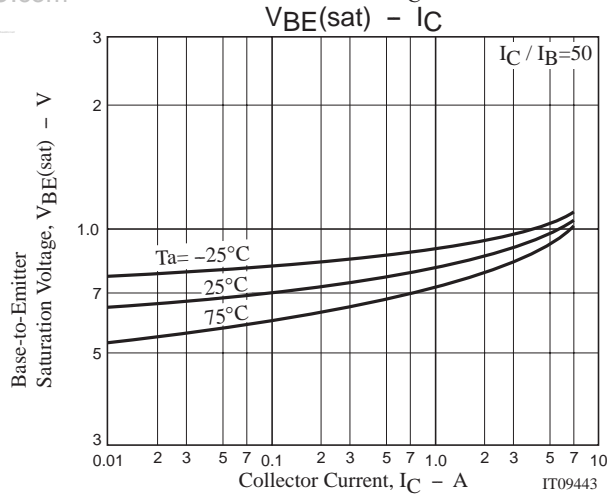
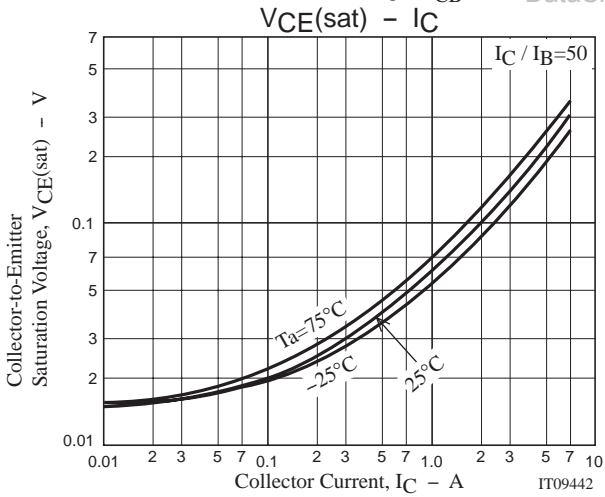
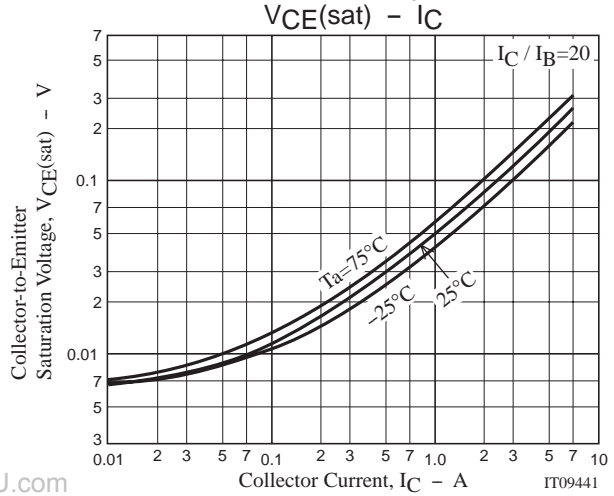
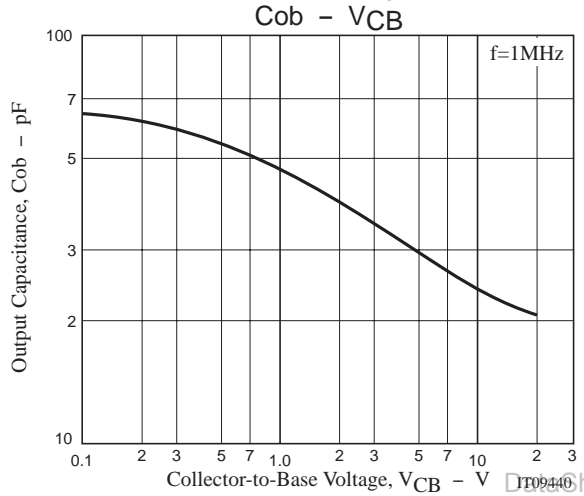
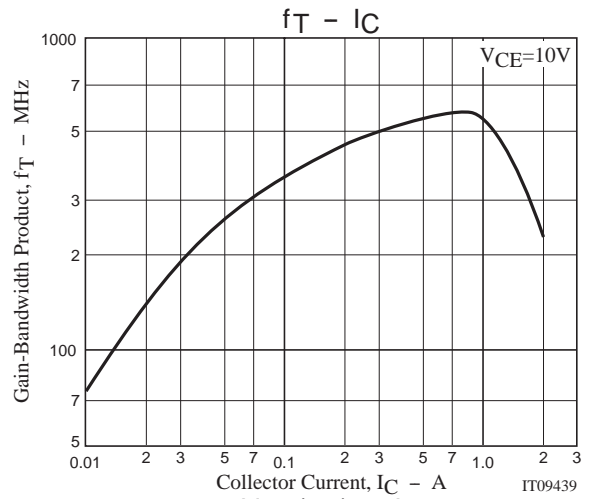
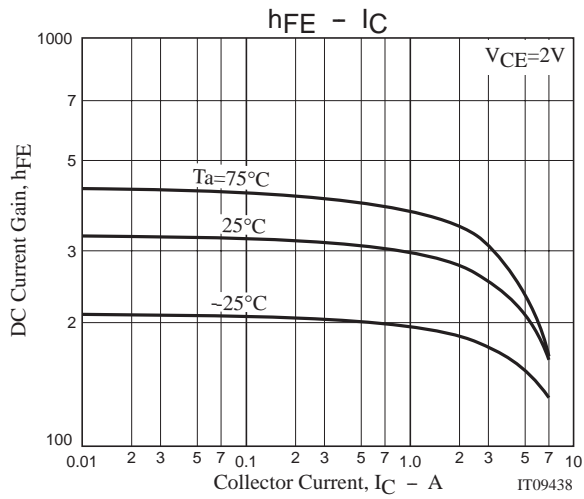
Switching Time Test Circuit



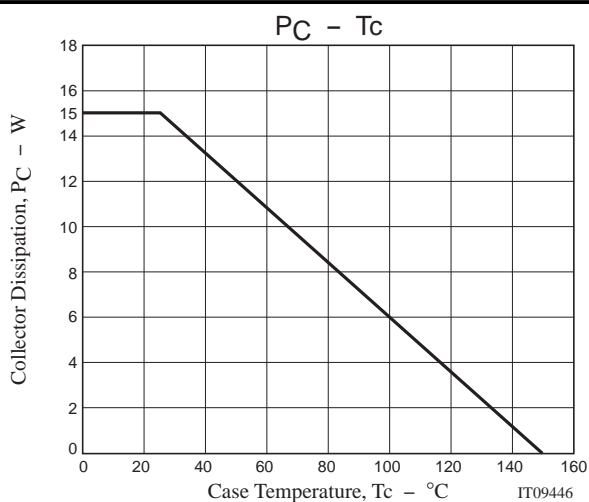
$$I_C = 20I_{B1} = -20I_{B2} = 3A$$



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